

generating a plasma of said ashing gas by applying a voltage between said first and second electrodes wherein at each said at least one inlet said plasma extends from the first electrode toward the second electrode and at each said at least one inlet a cross section of the plasma has a length along the first direction and a width along a second direction perpendicular to the first direction and parallel to the electrodes where the length is longer than the width;

placing a substrate between said first and second electrodes;
ashing a material over the substrate by the plasma of said etching gas; and
changing a relative location of the substrate with respect to the plasma in the second direction during the etching.

F1
Uncl
⁴³
~~84~~. (New) The process according to claim ~~83~~⁴² wherein a pressure in said reaction chamber is from 0.1 to 800 Torr.

⁴⁴
~~85~~. (New) The process according to claim ~~83~~⁴² wherein said material is a resist.

⁴⁵
~~86~~. (New) The process according to claim ~~83~~⁴² wherein said substrate is a glass substrate.

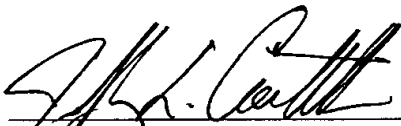
REMARKS

Applicants hereby add claims 73-86 to more completely set forth the scope of the invention. Applicants wish to bring to the Examiner's attention that the limitation of the plurality of gas inlets arranged in a first direction and the plasma of which cross section is elongated in the first direction (as recited in claim 73) is supported by the specification at page 8, first paragraph.

Examination on the merits is respectfully requested.

If a conference would expedite prosecution of the instant application, the Examiner is hereby invited to telephone the undersigned to arrange such a conference.

Respectfully submitted,



Jeffrey L. Costellia
Registration No. 35,483

NIXON PEABODY LLP
8180 Greensboro Drive, Suite 800
McLean, VA 22102
(703) 770-9300